

Electronic Acknowledgement Receipt

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International Application Number:	
Confirmation Number:	2319
Title of Invention:	Stacked structure and production method thereof
First Named Inventor/Applicant Name:	Hubert Moriceau
Customer Number:	90678
Filer:	Jasper W. Dockrey
Filer Authorized By:	
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Application Type:	U.S. National Stage under 35 USC 371

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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/Message Digest	Multi Part/.zip	Pages (if appl.)
1	NPL Documents	Demeester_et_al_Epitaxial_Lift-Off_and_Its_Aplns.pdf	1057147 e514a67ef257a1b59cd7bd60d39af05986a 40b7c	no	13

Warnings:

Information:

2	NPL Documents	Denteneer_et_al_Hydrogen_Diffusion_and_Passivation_of_Shallow_Impurities.pdf	299205 9a4be7616268e450c107930a24c1956759a 6b8ba	no	5
Warnings:					
Information:					
3	NPL Documents	Denteneer_et_al_Structure_and_Properties_of_Hydrogen-Impurity_Pairs.pdf	342276 a91ff56edf7086aa9e74cdcaf8287aa5ee12 a8a	no	4
Warnings:					
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4	NPL Documents	DiCioccio_et_al_Silicon_Carbide_on_Insulator_Formation.pdf	130526 f3f564678f1bb826e45d975574c99b298909 2ac4	no	2
Warnings:					
Information:					
5	NPL Documents	Dirks_AG_et_al_Columnar_Microstructure_in_Vapor_Deposited_Thin_Films.pdf	1187199 6b089b5565b3ccbe5389aaa781ca71cc23e 78fc0	no	15
Warnings:					
Information:					
6	NPL Documents	Duo_et_al_Comparison_Between_The_Different.pdf	821079 6519e4d26a98aed37e9d54f06b517ddab7 ea02d	no	6
Warnings:					
Information:					
7	NPL Documents	Duo-et-al-Evolution-of-Hydrogen-and-Helium_1.PDF	549396 0e37d771df074bcdd56fba107f0f36ae063f 281a	no	6
Warnings:					
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8	NPL Documents	Eaglesham_White_et_al_Equilibrium_Shape_of_Si.pdf	272298 5602f2e891fc72813254578fc7de7e3d22 897b	no	4
Warnings:					
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9	NPL Documents	EerNisse_E-Compaction_of_Ion-Implanted_Fused_Silica.pdf	768866 8a4542aa7694733b33057fc7d297c153ff171 1c2	no	8
Warnings:					
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10	NPL Documents	EerNisse_EP-Role_of_Integrated_Lateral_Stress_In_Surface_Deformation_of_HeImplanted_Surfaces.pdf	801341 c1c625f6e6ad75561111b6a2253dc5f79cd4 1a70	no	9
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11	NPL Documents	Evans_JH_An_Interbubble_Fracture_Mechanism_Of_Blister.pdf	869679 da7e36616b7161668c796ee119344efcfde789bb	no	12
Warnings:					
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12	NPL Documents	Feijoo_et_al-Prestressing_of_Bonded.pdf	390788 6e4546b0647157aca4b2ed11123fd63bbbe1fd43	no	9
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13	NPL Documents	Feng_et_al_Generalized_Formula_For_Curvature.pdf	137308 7b69fb79763717ee52a4a8a8e9bf851b2905415	no	3
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14	NPL Documents	Garner_DM-The_Fabrication_Of_A_Partial_SOI_Substrate.pdf	376649 3ab2d6c6d9647a91290089da18080db2635f5024	no	6
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15	NPL Documents	Gerasimenko_N-Infrared_Absorption_of_Silicon_Irradiated_by_Phrotons.pdf	423407 0ba07b0abd376be9dc6753daab01e32fe3c2edc2	no	7
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16	NPL Documents	Ghandi_Sorab-VSLI_Fabrication_Principles-Silicon_and_Gallium_Arsenide.pdf	145184 deb5206b7d6a70e5146e8c11fa0ff80141e7917	no	4
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17	NPL Documents	Greenwald_AC-Pulsed-Electron-Beam_Annealing_of_Ion-Implantation_Damage.pdf	364299 284ac2ea755b2373605663f33312b5af2416d0aa	no	4
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18	NPL Documents	Grovenor_C_Microelectronic_Materials.pdf	183072 d4bd9c4d295257fb1e504f92e143fc307942099	no	5
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19	NPL Documents	GuilhalmenC_C_et_al_Characterization_By_Atomic_Force_Microscopy_of_the_SOI_Layer.pdf	266316 de8b968045badcb478006f2b74b1b3bbdb55eb3	no	4
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20	NPL Documents	Haisma_et_al_Silicon_on_Insulator-Wafer_Bonding.pdf	1279237 3c39435ab09822e0abf405965b5f0aef3c8ba2e7	no	18
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21	NPL Documents	Hamaguchi_et_al_Device_Layer_Transfer_Technique.pdf	157984 ef26f17472e6db1c245cd8d154a67fb605e5a1ba	no	3
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22	NPL Documents	Hamaguchi_et_al_Novel_LSI-SOI_Wafer.pdf	308961 bd2819f285b888256918579a21f3095a1058db8f	no	4
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23	NPL Documents	Henttinen_et_al-Mechanically_Induced_Si_Layer.pdf	248942 084a59899bac7d2b8d9a6613752add4294e93ae3	no	3
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24	NPL Documents	Hulett_DM_et_al_Ion_Nitriding_and_Ion_Impantation.pdf	228302 f894673d4381b7976ede884eb3589dad03934092	no	4
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25	NPL Documents	IBM_Technical_Disclosure_Bulletin-Isolation_By_Inert_Ion_Implantation.pdf	31620 6d441e872faf56aea6a339eab8aac6aec66176c	no	1
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26	NPL Documents	IBM-Tech-Disclosure-SOI-Interposer.PDF	135377 a0bd769b824620685b9bdf1738e37b02fd4db8a1	no	5
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27	NPL Documents	Jap-OA-Dated-10-25-07-2002-581572.pdf	209378 a150ec5658266e19d62f54064cf2c605eea9a495	no	5
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28	NPL Documents	Jaussaud_C_et_al-Microstructure_of_Silicon_Implanted_With_High_Dose_Oxygen_Ions.pdf	393224 fbcf5ae0b610d798f76fcfd6338055485e0fe4e11	no	3
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29	NPL Documents	Johnson-High_Fluence_Deuteron_Bombardment_of_Silicon.pdf	837642 4618f06ca21720f7eb3f97a2d5d022d69f6ef47f	no	9
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30	NPL Documents	Jones_KS_et_al-A_Systematic_Analysis_of_Defects_in_Ion_Implanted_Silicon.pdf	2789593 cc854ef38b35faa8eac5a958f3cd440569de00b	no	35
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31	NPL Documents	Jones_et_al_Enhanced_elimination_of_implantation_damage_upon_exceeding_the_solid_solubility.pdf	379786 d346990b4884595096dba89caa0d8f3875d705	no	4
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32	NPL Documents	Kamada_et_al-Observation_of_Blistering_and_Amorphization_on_Germanium_Surface_After_keV.pdf	519461 b84feea9b5e30bde84030fbfb65e6c3fd318d3ef	no	6
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33	NPL Documents	Klem_Characteristics_of_Lift.pdf	393669 10ac698a9981860788adbf0daa4c5b943f7fc900	no	6
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34	NPL Documents	Komarov_et_al-Crytallographic_Nature_and_Formation_Mechanisms_of_Highly_Irregular_Structure.pdf	687131 09abcd049eec0cb5ef018ab92d398cda91581fe	no	9
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35	NPL Documents	Kucheyev_et_al-Ion_Implantation_Into_GaN.pdf	3044381 c815f5ca1668f25437c8b8e0c849641260f98073	no	58
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36	NPL Documents	Laporte-A-et-al-Charged-Defects-at-the-Interface.pdf	1355175 467416890ffe48a14db995a89ddbf3bb3b39de5e	no	5
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38	NPL Documents	Ligeon_E-Hydrogen_Implantation_in_Silicon_Between_1-5_and_60_KeV.pdf	820674 27bfc18c1ad21c58a1c0a47282bd33459a2ccab1	no	9
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39	NPL Documents	Liu_et_al-Ion_Implantation_in_GaN_at_Liquid-Nitrogen_Temperature.pdf	461874 e98f5850b8c00282315a65649bb505c19ea bb80	no	6
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41	NPL Documents	Maleville-et-al-Physical-Phenomena-Involved_1.PDF	843600 4a6da6e5c42447e66afc491917ca24916d9 0c244	no	18
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42	NPL Documents	Maleville_C_Wafer_Bonding_and_High-Implantation.pdf	266110 47c85fa696b27cfad7abd3c57423cfa0bba0 3ba3	no	6
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43	NPL Documents	Manuaba_A-Comparative_Study_on_Fe_Ni_Cr_P_Metallic_Glass_and_Its_Polycrystalline_Modification.pdf	1160732 493a4c311b0adf850eda5975c840ac491a4 3b9a5	no	11
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44	NPL Documents	Matsuda_et_al_Large_Diameter_Ion_Beam_Implantation_System.pdf	129012 f47a95c5000c122f0f8c5f6ce23b1c01b972d 2e2	no	3
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45	NPL Documents	Matsuo_et_al_Abnormal_solid_solution_and_activation_behavior_in_GA-implanted_Si100.pdf	207625 9945d4f3bd57fde9c6b695e8e4ac87f8144f 0ff	no	3
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46	NPL Documents	Mishima_Y_and_T_Yagishita_Investigation_Of_The_Bubble_Formation.pdf	165000 6fb7fc6f1210be7216bb64bf04cb3b26f6f6 8d2	no	3
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47	NPL Documents	Miyagawa_S_et_al-Helium_Reemission_During_Implantation_of_Silicon_Carbide.pdf	375866 eab902866e830477d3cd2a9e7c5876d4540 8749	no	5
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48	NPL Documents	Miyagawa_S_et_al-Surface_Structures_of_Silicon_Carbide_Irradiated_With_Helium_Ions.pdf	774178 c7f2a33342d848c7f5c65737bb161857f947 ea8d	no	9
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49	NPL Documents	Monemar_B-Shallow_Impurities_in_Semiconductors.pdf	485747 add11312cdf8fb9227d8c8e17710ed952c9 5e94	no	6
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50	NPL Documents	Moreau_Wayne_M_Semiconductor_Lithography_Principles.pdf	497940 9d914d61451ef12e7c742510ac2569aeb2 acfcb	no	17
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51	NPL Documents	Moriceau_H_et_al_A_New_Characterization_Process_Used_To.pdf	303042 0cf0df4d02bddd8c35e74961e6bb62d25 35700	no	6
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52	NPL Documents	Moriceau_H_et_al_Cleaning_and_Polishing_As_Kep_Steps.pdf	151493 0e3dee0395b4e959235a05b25f562e47a6e eec96	no	2
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53	NPL Documents	Moriceau_H_et_al_The_Smart_Cut_Process_As_A_Way_To.pdf	116346 bad8a36386cc6833845194eac20c2917c9ba ec871	no	2
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54	NPL Documents	Moriceau_Vol99-1_Meeting_Abstract.pdf	156085 a84e0749dacf4639868a50f220d80df795eb 7a8b	no	2
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55	NPL Documents	Munteanu-et-al-Detailed-Characteristics-of-Unibond-Material.pdf	186594 083f9c1aca59b031c052ae265134352348f a52a	no	4
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56	NPL Documents	Myers_DR-The_Effects_of_Ion-Implantation_Damage_on_The_First_Order_Raman_Spectra.pdf	676976 58022efa3c3a0c9831528800a03bd1b7e34 d2f7c	no	7
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57	NPL Documents	Neethling_CE_et_al-Identification_of_Hydrogen_Plantelets_in_Proton_Bombardment_GaAs.pdf	436026 b8cb55df54886caf519b51482af2c80778 0197	no	5
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58	NPL Documents	Nichols_C_et_al_Properties_of_Hydrogen_in_Crystalline_Silicon.pdf	740397 16eb72d90c4ec2b7d57db6c180d2ea0d18 c5bd78	no	4
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59	NPL Documents	Nicoletti_S_et_al_Bi-Epitaxial_YBCO_Grain_Boundary_Josephson_Junctions.pdf	869860 06a47a30171ce37d689712bbd7925f8e873 df226	no	13
Warnings:					
Information:					
Total Files Size (in bytes):				32502614	
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p>New Applications Under 35 U.S.C. 111 If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p>National Stage of an International Application under 35 U.S.C. 371 If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p> <p>New International Application Filed with the USPTO as a Receiving Office If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.</p>					